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(57) Abstract :

The present invention relates to the α Drain Current • enhancement for Output Characteristics Improvement of MOSFET. Drain current determines the performance of MOSFET. High value of drain current shows the better device performance which is designed using MOSFET. The replacement of discrete electronics circuit from IC technology is providing an outstanding result by mini attenuation with size and low power dissipation, by maintaining the cost and speed factor, for a desired system. MOSFET is treated as a backbone of IC Technology. So by improving the output characteristics of MOSFET, new technology node can be created with improved performance or by adding some more functionality into existing technology node. In order to enhance the drain current, a method has been proposed. In this proposed method, all the device parameters are compared which shows their direct dependency on Drain current calculation and a perfect parameter is extracted to enhance the drain current of MOSFET.

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